



Shenzhen Tuofeng Semiconductor Technology Co., Ltd

**N - CHANNEL ENHANCEMENT MODE POWER MOSFET**

SGT MOS、低内阻、低结电容开关损耗小

**TF040N06NG****• General Description**

The TF040N06NG uses advanced trench technology and design to provide excellent RDS(ON) with low gate charge. It can be used in a wide variety of applications.

**• Features**

Advance device construction

Low  $R_{DS(ON)}$  to minimize conduction loss

Low Gate Charge for fast switching

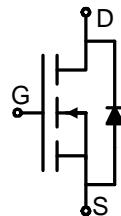
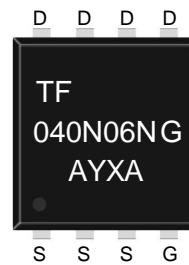
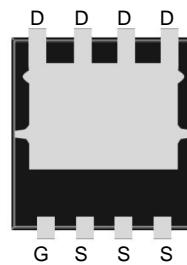
Low Thermal resistance

**• Application**

Synchronous Rectification for AC-DC/DC-DC

converter

Power Tools

**• Product Summary** $V_{DS} = 60V$   $I_D = 100A$  $R_{DS(ON)(10V\ typ)} = 3.9m\Omega$  $R_{DS(ON)(4.5V\ typ)} = 5.3m\Omega$ **PDFNWB5x6-8L****• Package Marking and Ordering Information:**

Part NO.	TF040N06NG
Marking1	040N06NG
Marking2	TF:tuofeng; AA:device code; Y:year code; X:Week
Basic ordering unit	5000 / PCS

**• Absolute Maximum Ratings ( $T_C = 25^\circ C$ )**

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DS}$	60	V
Gate-Source Voltage	$V_{GS}$	$\pm 20$	V
Continuous Drain Current	$I_D @ T_C = 25^\circ C$	100	A
	$I_D @ T_C = 75^\circ C$	70	A
	$I_D @ T_C = 100^\circ C$	60	A
Pulsed Drain Current <sup>①</sup>	$I_{DM}$	270	A
Total Power Dissipation	$P_D @ T_C = 25^\circ C$	85	W
Total Power Dissipation	$P_D @ T_A = 25^\circ C$	2.0	W
Operating Junction Temperature	$T_J$	-55 to 150	$^\circ C$
Storage Temperature	$T_{STG}$	-55 to 150	$^\circ C$
Single Pulse Avalanche Energy	$E_{AS}$	110	mJ



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### • Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	R <sub>thJC</sub>	-	-	3.5	° C/W
Thermal resistance, junction - ambient	R <sub>thJA</sub>	-	-	33	° C/W
Soldering temperature, wavesoldering for 8 s	T <sub>sold</sub>	-	-	265	° C

### • Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	60	-	-	V
Gate Threshold Voltage	V <sub>GS(TH)</sub>	V <sub>GS</sub> = V <sub>DS</sub> , I <sub>D</sub> = 250μA	1.2	1.8	2.5	V
Drain-Source Leakage Current	I <sub>DSS</sub>	V <sub>DS</sub> =60 V <sub>GS</sub> = 0V	-	-	1.0	μA
Gate- Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V , V <sub>DS</sub> = 0V	-	-	±100	nA
Static Drain-source On Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =20A	-	3.9	5.5	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =15A	-	5.3	7.0	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> = 25V, I <sub>D</sub> =20A	-	20	-	S
Source-drain voltage	V <sub>SD</sub>	I <sub>S</sub> =20A	-	-	1.20	V

### • Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C <sub>iss</sub>	f = 1MHz V <sub>DS</sub> =30V	-	1957	-	pF
Output capacitance	C <sub>oss</sub>		-	415	-	
Reverse transfer capacitance	C <sub>rss</sub>		-	15.5	-	

### • Gate Charge characteristics(T<sub>a</sub> = 25°C)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q <sub>g</sub>	V <sub>DD</sub> = 30V I <sub>D</sub> = 20A V <sub>GS</sub> = 10V	-	33	-	nC
Gate - Source charge	Q <sub>gs</sub>		-	5.5	-	
Gate - Drain charge	Q <sub>gd</sub>		-	6.2	-	

Note: ① Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2% ;



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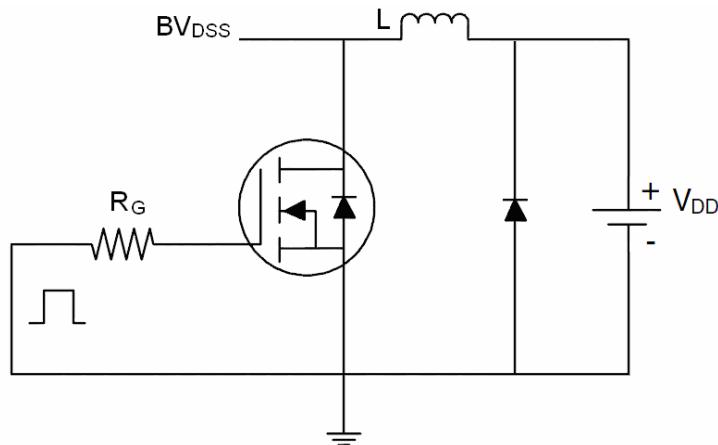
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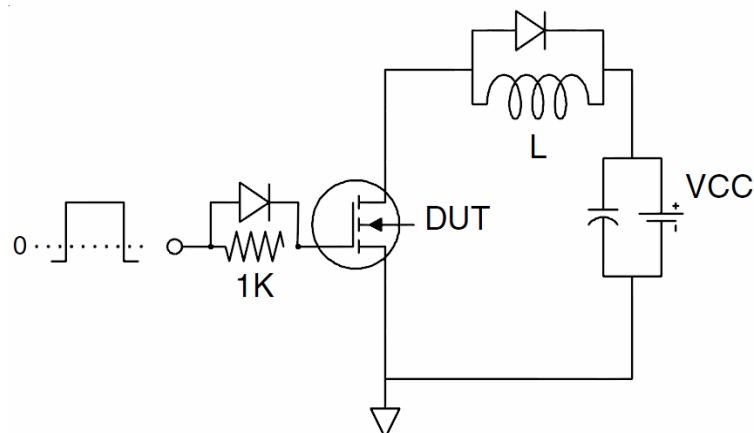
**TF040N06NG**

### Test Circuit

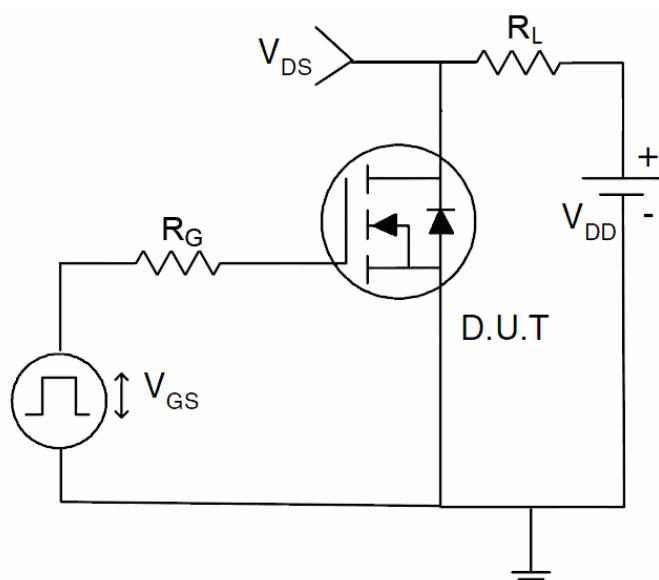
#### 1) E<sub>AS</sub> test Circuit



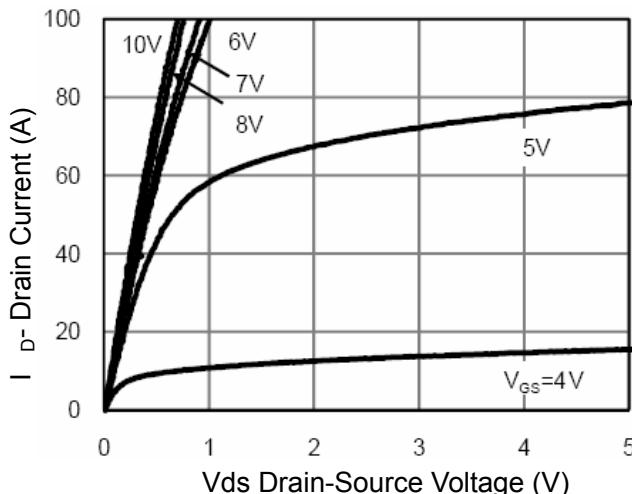
#### 2) Gate charge test Circuit



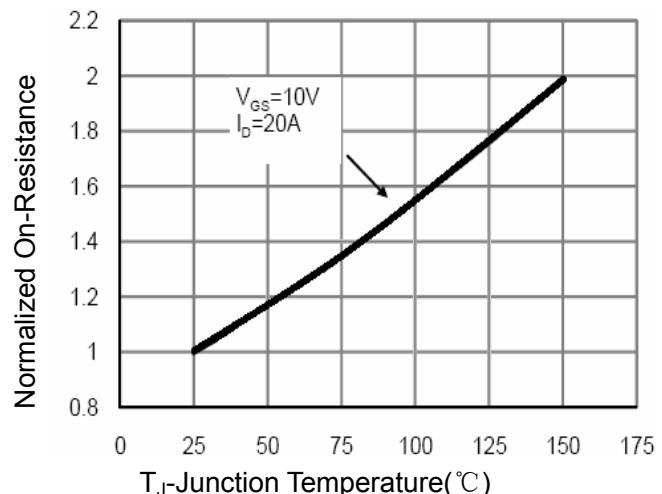
#### 3) Switch Time Test Circuit



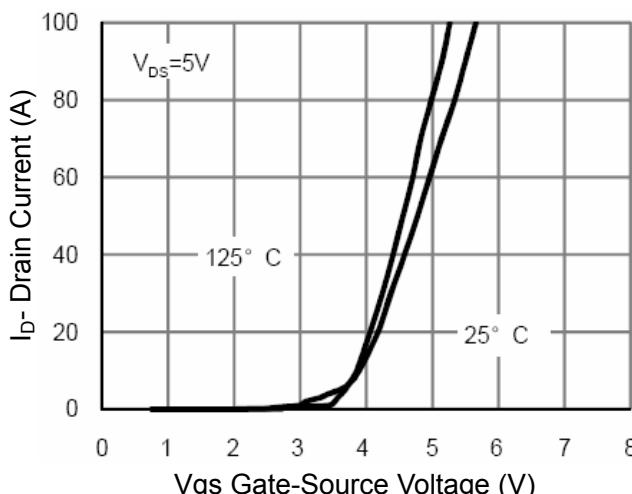
**Typical Electrical and Thermal Characteristics**



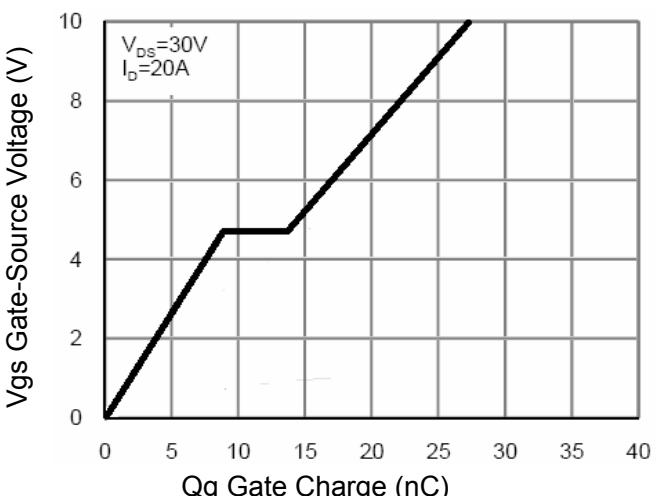
**Figure 1 Output Characteristics**



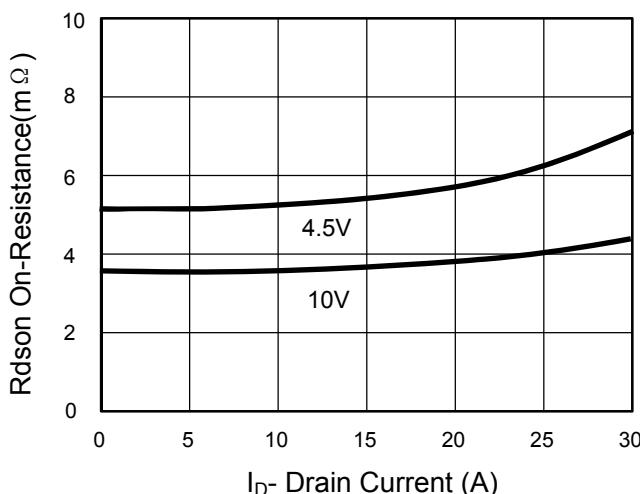
**Figure 4 Rdson-JunctionTemperature**



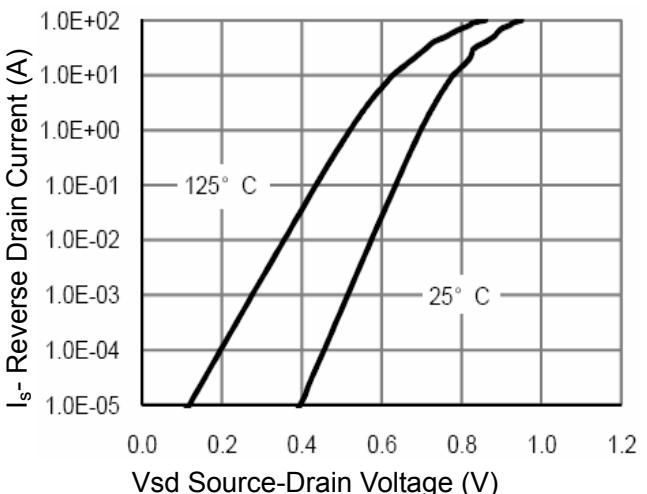
**Figure 2 Transfer Characteristics**



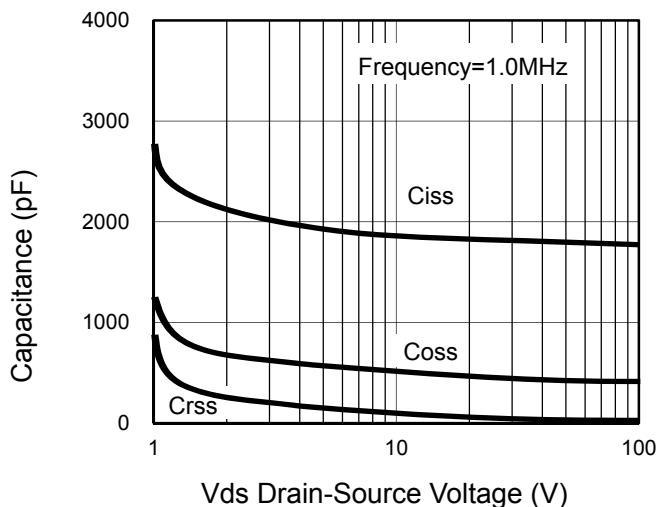
**Figure 5 Gate Charge**



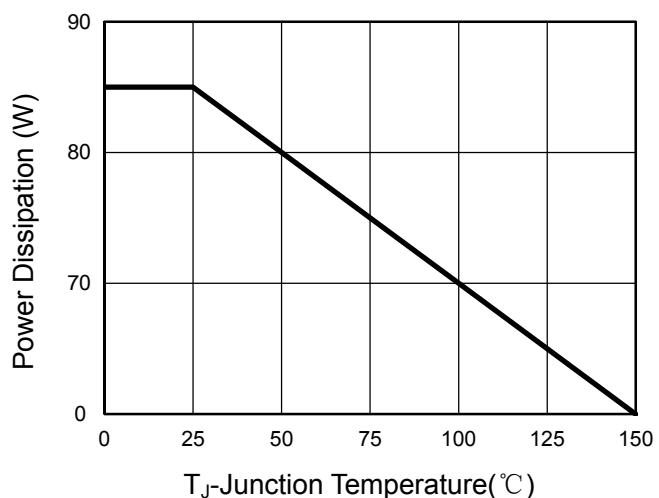
**Figure 3 Rdson- Drain Current**



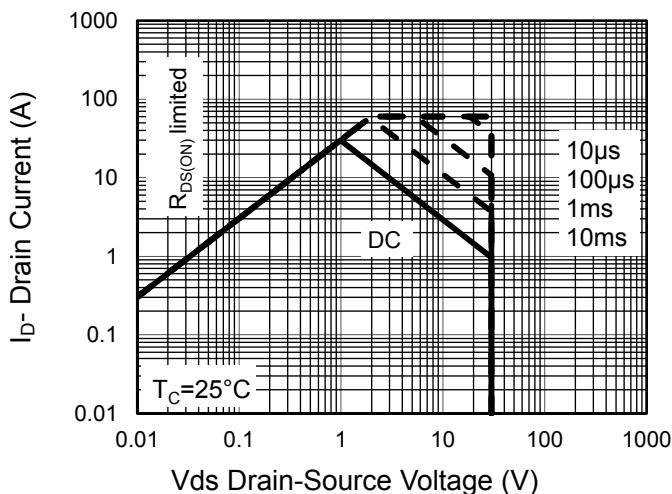
**Figure 6 Source- Drain Diode Forward**



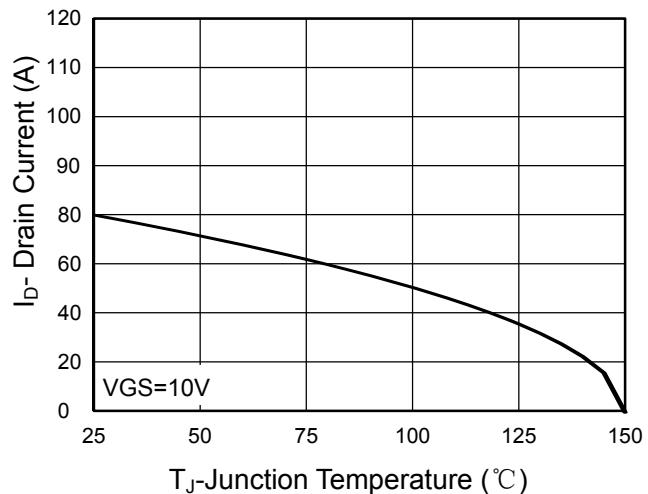
**Figure 7 Capacitance vs Vds**



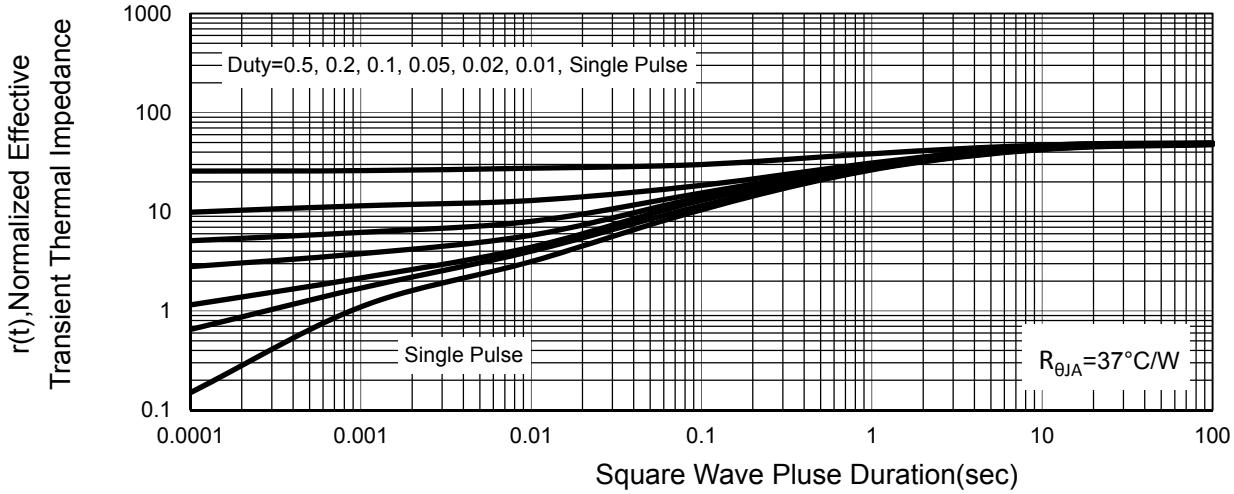
**Figure 9 Power De-rating**



**Figure 8 Safe Operation Area**



**Figure 10 Current De-rating**



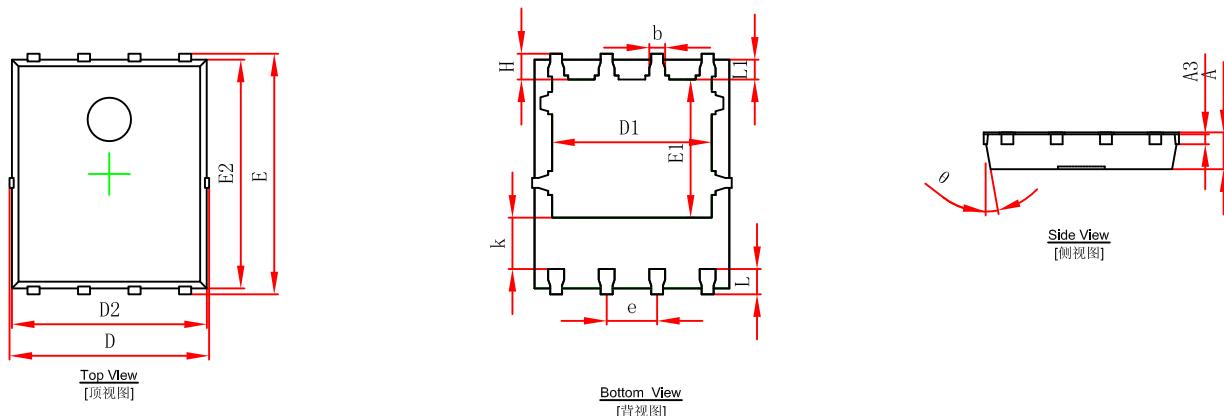
**Figure 11 Normalized Maximum Transient Thermal Impedance**



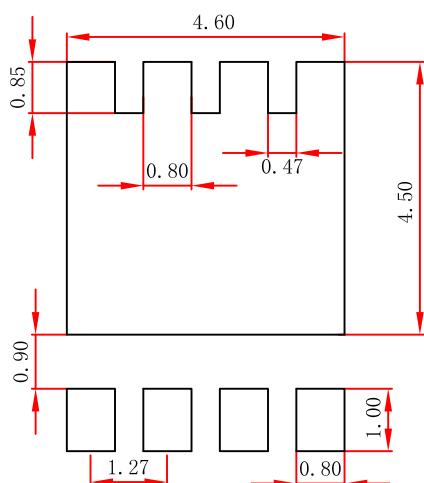
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**TF040N06NG****PDFNWB5x6-8L Package Outline Dimensions**

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.254REF.		0.010REF.	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	3.910	4.110	0.154	0.162
E1	3.375	3.575	0.133	0.141
D2	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP.		0.050TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
θ	10°	12°	10°	12°

**PDFNWB5x6-8L Suggested Pad Layout****Note:**

1. Controlling dimension:in millimeters.
2. General tolerance: $\pm 0.05\text{mm}$ .
3. The pad layout is for reference purposes only.